12V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
-12V	11mΩ @ V_{GS} = -4.5V	-26A
	14mΩ @ V_{GS} = -3.7V	-23A
	19mΩ @ V_{GS} = -2.5V	-20A
	30mΩ @ V_{GS} = -1.8V	-16A

Features

- 0.6mm Profile – Ideal for Low-Profile Applications
- PCB Footprint of 4mm^2
- Low Gate Threshold Voltage
- Low On-Resistance
- Wettable Flank for Improved Optical Inspection
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Description and Applications

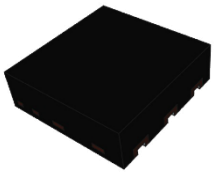
This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Power-management functions
- General-purpose interfacing switches

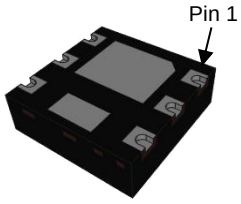
Mechanical Data

- Package: U-DFN2020-6
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.0065 grams (Approximate)

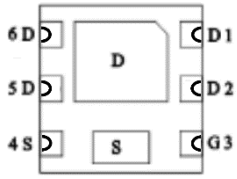
U-DFN2020-6/SWP (Type UXG)



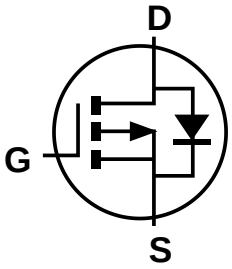
Top View



Bottom View



Pinout
Bottom View



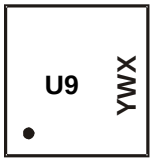
Equivalent Circuit

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMP1009UFDFW-7	U-DFN2020-6/SWP (Type UXG)	3,000	Tape & Reel
DMP1009UFDFW-13	U-DFN2020-6/SWP (Type UXG)	10,000	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



U9 = Product Type Marking Code
YWX = Date Code Marking
Y = Year (ex: 5 = 2025)
W = Week (ex: a = Week 27; z Represents Week 52 and 53)
X = Internal Code (ex: U = Monday)

Date Code Key

Year	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034	2035
Code	4	5	6	7	8	9	0	1	2	3	4	5

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-12	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 5) V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	-10 -8.3	A
Continuous Drain Current (Note 6) V_{GS} = -4.5V	Steady State	T_C = +25°C T_C = +70°C	I_D	-26 -21	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-79	A
Maximum Body Diode Continuous Current (Note 5)			I_S	-1.8	A
Avalanche Current (Note 7) L = 0.1mH			I_{AS}	-30	A
Avalanche Energy (Note 7) L = 0.1mH			E_{AS}	45	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 8)	T_A = +25°C	P_D	1.2	W
Thermal Resistance, Junction to Ambient (Note 8)	Steady State	$R_{\theta JA}$	102	°C/W
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	1.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	69	°C/W
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{\theta JC}$	11	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	-12	—	—	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1	μA	V_{DS} = -9.6V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.3	—	-1.0	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	8	11	mΩ	V_{GS} = -4.5V, I_D = -5A
		—	9	14		V_{GS} = -3.7V, I_D = -5A
		—	12	19		V_{GS} = -2.5V, I_D = -4A
		—	19	30		V_{GS} = -1.8V, I_D = -1A
Diode Forward Voltage	V_{SD}	—	-8	-1.2	V	V_{GS} = 0V, I_S = -10A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	—	1860	—	pF	V_{DS} = -10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	498	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	416	—	pF	
Gate Resistance	R_g	—	11	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	26	—	nC	V_{DS} = -6V, I_D = -10A
Total Gate Charge (V_{GS} = -8V)	Q_g	—	44	—	nC	
Gate-Source Charge	Q_{gs}	—	3.3	—	nC	
Gate-Drain Charge	Q_{gd}	—	8.1	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	7.0	—	ns	V_{DS} = -6V, V_{GS} = -4.5V R_G = 1Ω, I_D = -8A
Turn-On Rise Time	t_R	—	10.6	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	62.2	—	ns	
Turn-Off Fall Time	t_F	—	61	—	ns	
Reverse-Recovery Time	t_{RR}	—	34.4	—	ns	I_F = -12A, di/dt = 500A/μs
Reverse-Recovery Charge	Q_{RR}	—	28.1	—	nC	

Notes: 9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

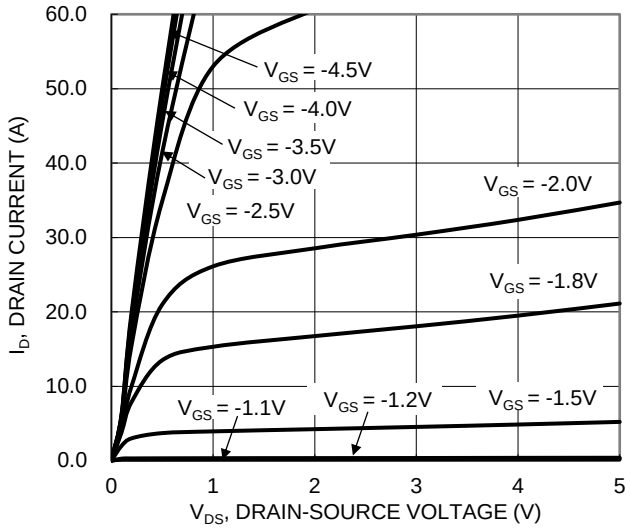


Figure 1. Typical Output Characteristic

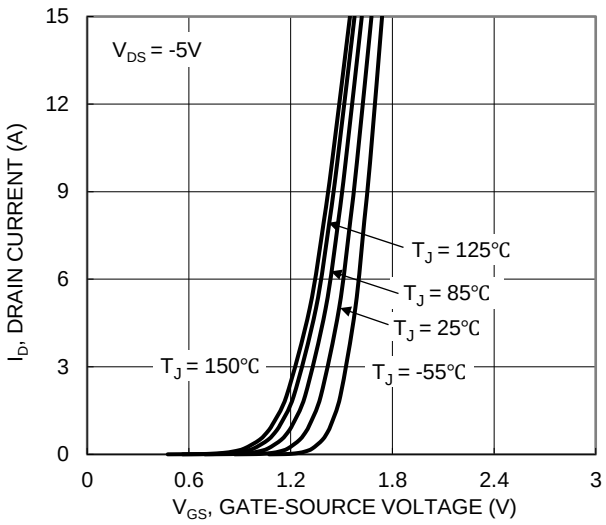


Figure 2. Typical Transfer Characteristic

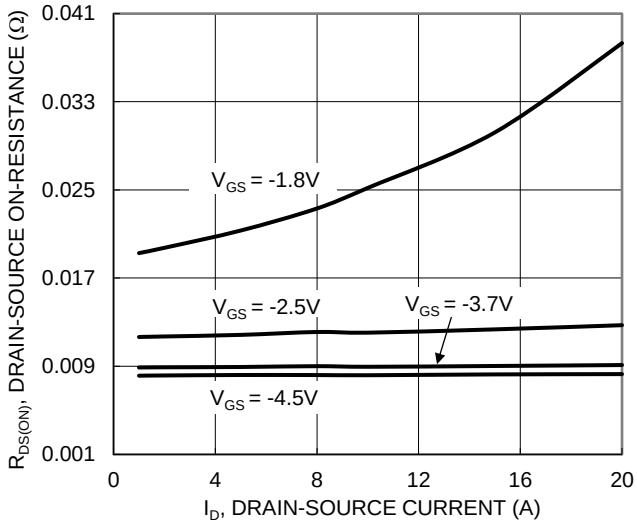


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

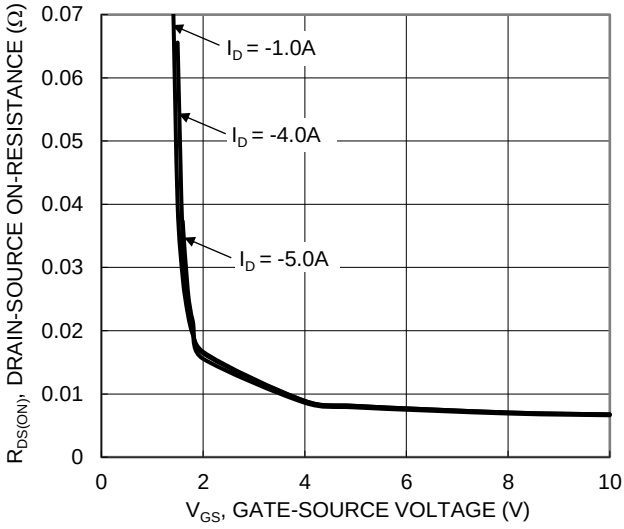


Figure 4. Typical Transfer Characteristic

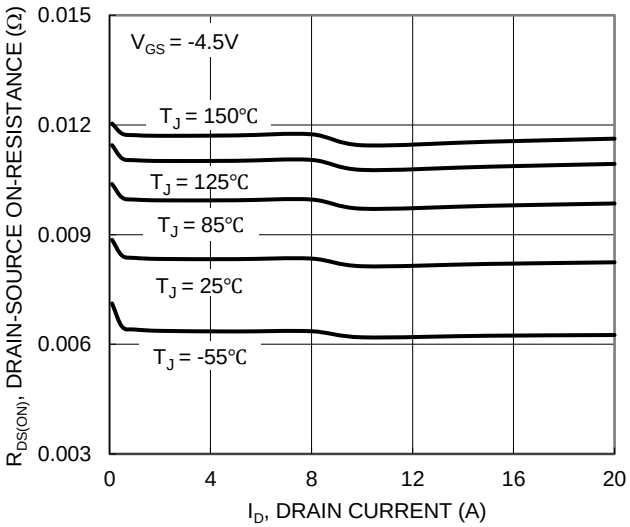


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

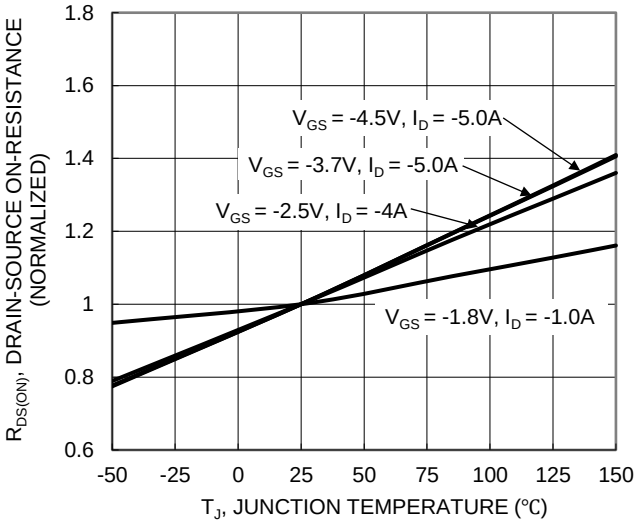


Figure 6. On-Resistance Variation with Junction Temperature

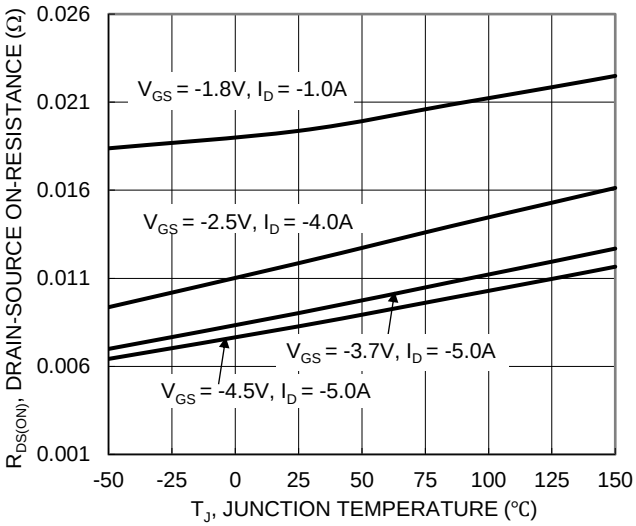


Figure 7. On-Resistance Variation with Junction Temperature

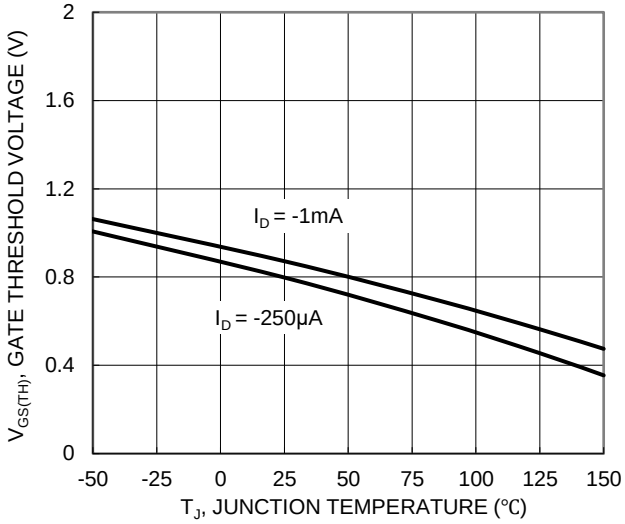


Figure 8. Gate Threshold Variation vs. Junciton Temperature

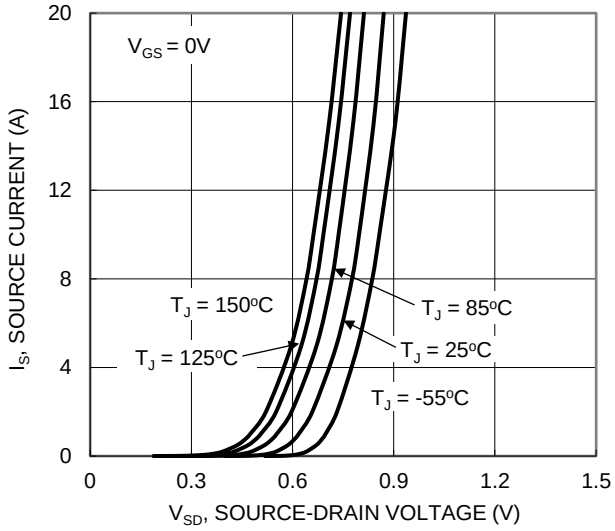


Figure 9. Diode Forward Voltage vs. Current

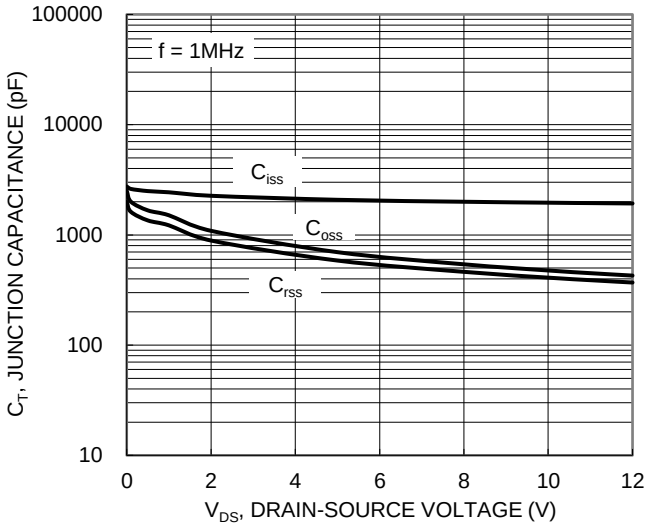


Figure 10. Typical Junction Capacitance

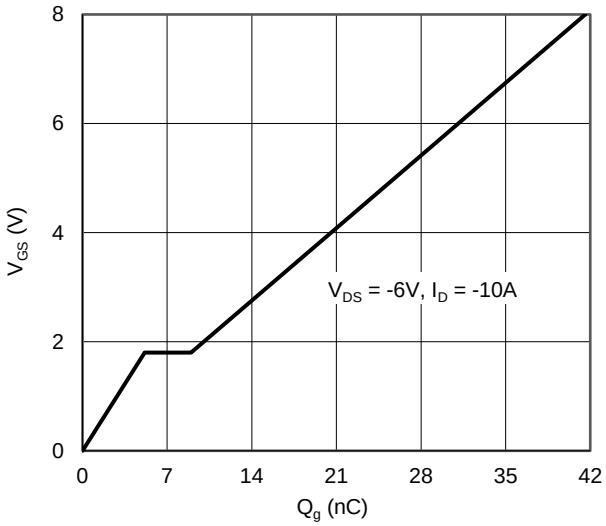


Figure 11. Gate Charge

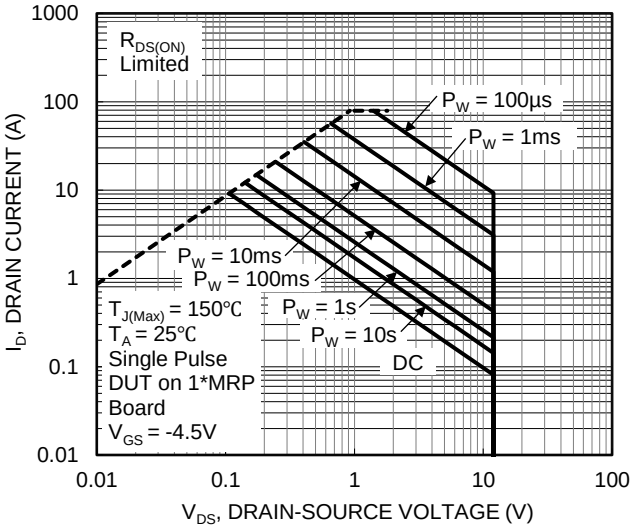


Figure 12. SOA, Safe Operation Area

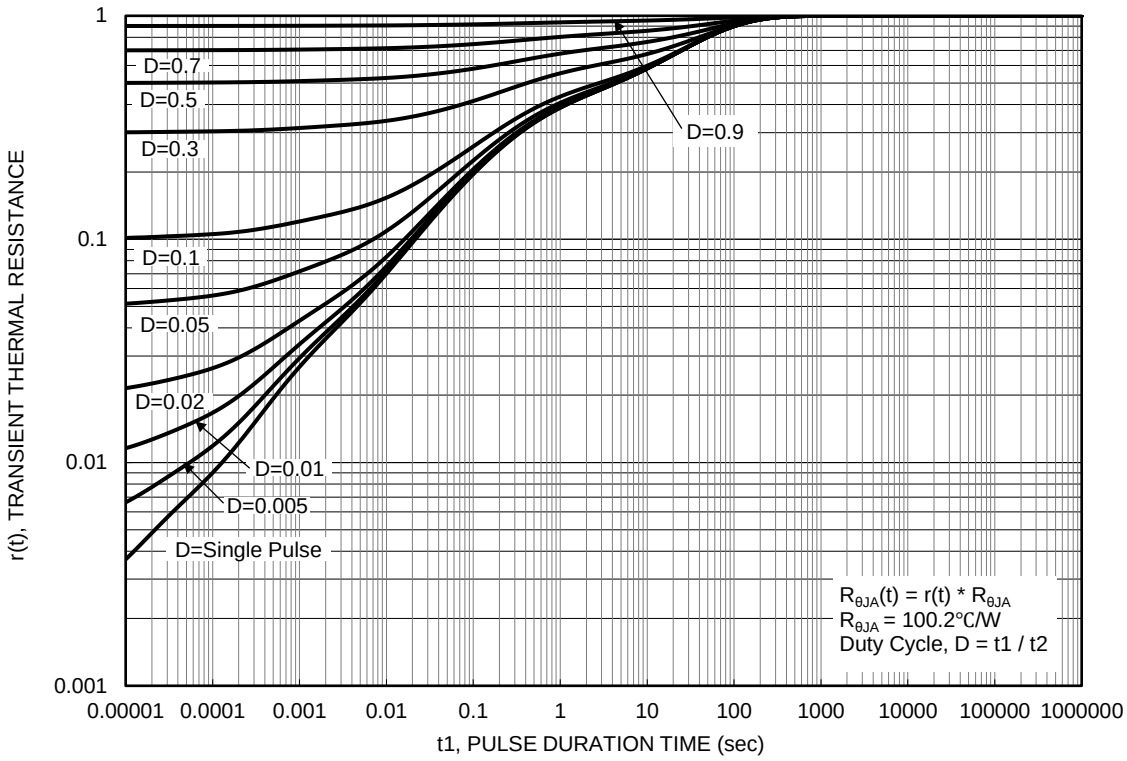
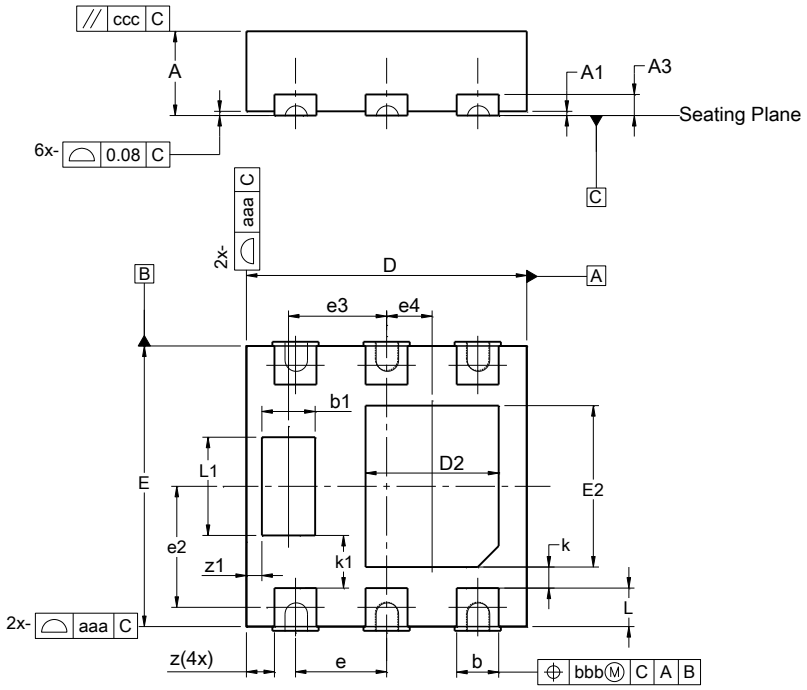


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6/SWP (Type UXG)

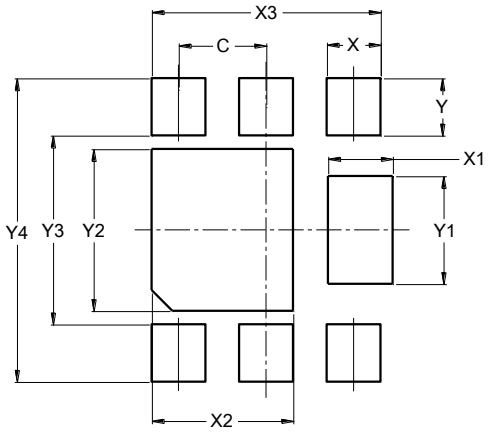


U-DFN2020-6/SWP (Type UXG)			
Dim	**Min**	**Max**	**Typ**
A	0.59	0.65	0.62
A1	0.00	0.05	0.03
A3	—	—	0.152
b	0.28	0.38	0.33
b1	0.35	0.45	0.40
D	1.95	2.05	2.00
D2	0.87	1.07	0.97
E	1.95	2.05	2.00
E2	1.07	1.27	1.17
e	0.65 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
L	0.225	0.325	0.275
L1	0.67	0.77	0.72
k	—	—	0.15
k1	—	—	0.375
z	—	—	0.20
z1	—	—	0.11
aaa	0.25		
bbb	0.10		
ccc	0.10		
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6/SWP (Type UXG)



Dimensions	Value (in mm)
C	0.650
X	0.350
X1	0.480
X2	1.050
X3	1.700
Y	0.425
Y1	0.800
Y2	1.200
Y3	1.400
Y4	2.250

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